

**FABRICATION OF GOLD NANODOT ON SILICON
SUBSTRATE BY SCANNING PROBE MICROSCOPY
AND ITS CHARACTERIZATION**

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ITS CHARACTERIZATION**

by

TEGUH DARSONO

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TABLE OF CONTENTS

Acknowledgments	ii
Table of Contents	iv
List of Tables	viii
List of Figures	ix
List Abbreviations	xxiv
List of Symbols	xxvii
Abstrak	xxxii
Abstract	xxxiv
 CHAPTER 1 – INTRODUCTION	
1.1 Introduction	1
1.2 Problem Statements	5
1.3 Objectives of the Research	8
1.4 Scope of Study	12
1.5 Structure of the Thesis	14
 CHAPTER 2 – LITERATURE REVIEW	
2.1 Introduction	15
2.2 Scanning Tunneling Microscopy	17
2.3 Atomic Force Microscopy	20
2.3.1 Contact Mode	28
2.3.2 Non-contact Mode	30
2.3.3 Intermittent Contact (Tapping Mode)	39
2.3.4 Conductive-Atomic Force Microscopy	42

2.4	Field Evaporation Deposition	48
2.5	Nanostructure Fabrication	55
2.5.1	STM Lithography (STML)	57
2.5.2	AFM Lithography (AFML)	63
2.6	Metal-Semiconductor (M-S) Contact	72
2.6.1	Introduction	72
2.6.2	Formation of Barrier	72
2.6.2.1	Ideal Condition	72
2.6.2.2	Surface States	75
2.6.2.3	Depletion Layer	77
2.6.3	Barrier Lowering	80
2.6.3.1	Schottky Effect	80
2.6.3.2	Dipole Lowering	84
2.6.4	Current Transport Process	85
2.6.4.1	Thermionic Emission	86
2.6.4.2	Field and Thermionic-Field Emission	88
2.6.5	Current-Voltage Characteristics	91
2.6.5.1	Forward Bias	91
2.6.5.2	Reverse Bias	93
2.6.6	Schottky Barrier Determination	95
2.6.6.1	Conventional Schottky Diode	95
2.6.6.2	Nanostructured Schottky Diode	97

CHAPTER 3 – MATERIALS AND METHODS

3.1	Introduction	102
3.2	Sample Preparation	102

3.2.1	Substrate	102
3.2.1	Cleaning Process	103
3.2.1.1	Ultrasonic Cleaning	104
3.2.1.2	RCA-1	104
3.2.1.3	RCA-2	105
3.2.1.4	HF Dipping	105
3.3	Instrument Configurations	106
3.3.1	AFM Setup	107
3.3.1.1	Scanner	107
3.3.1.2	Cantilever Tips	108
3.3.1.3	Environment	111
3.3.2	Voltage Source	112
3.4	Gold Nanodot Deposition	113
3.4.1	Calibration of the Cantilever Deflection	115
3.4.2	The Construction of Force-distance (F-d) Curve	117
3.4.3	Tip-sample Distance Control	118
3.4.4	Gold Nanodot Deposition Process	120
3.5	Characterizations	123
3.5.1	Physical Characterization	124
3.5.2	Electrical Characterization	126
3.6	Transport Parameter Determinations	127
3.6.1	Conventional Schottky Diodes	127
3.6.2	Nanostructured Schottky Diodes	130

CHAPTER 4 – RESULTS AND DISCUSSIONS

4.1	Introduction	136
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4.2	Tip-Sample Distance Control	136
4.3	Deposition Process	149
4.3.1	FESEM/EDX Result	149
4.3.2	Effect of Tip-sample Bias Voltage	151
4.3.3	Effect of Pulse Polarity	153
4.4	Effect of Voltage Pulse	156
4.4.1	Effect of Voltage Pulse Amplitude	157
4.4.2	Effect of Voltage Pulse Duration	162
4.4.3	Threshold Voltage.....	167
4.5	Electrical Characterization	169
4.5.1	The Effect of Diode Dimension	170
4.5.1.1	(<i>I-V</i>) Characteristics	172
4.5.2	The Effect o Temperature	183
4.5.2.1	(<i>I-V</i>) Characteristics	183
CHAPTER 5 – CONCLUSSIONS AND FUTURE WORKS		
5.1	Conclusions	191
5.2	Suggestions for Future Research Works	194
REFERENCES		195

LIST OF TABLES

	Page
Table 3.1 List of chemical materials for substrates cleaning process	103
Table 3.2 List of cantilever tip specification	110
Table 4.1 Summary of the calculation of the calibration constant (α) of PSD, based on the F - d curve	140
Table 4.2 The tip-sample separation changes due to the application of the bias voltage between 1-9 Volts	146
Table 4.3 Deposition Parameters and Dot dimensions. $V_{\text{PULSE}} = -22 \text{ V}$, -24 V and -26 V , $\Delta t_{\text{pulse}} = 3 \text{ ms}$	158
Table 4.4 Deposition Parameters and Dot dimensions. $V_{\text{PULSE}} = - (19 -$ $32) \text{ V}$ and $\Delta t_{\text{pulse}} = 3.0 \text{ ms}$	159
Table 4.5 Deposition Parameters and Dot dimensions. $V_{\text{PULSE}} = - 26 \text{ V}$ and $\Delta t_{\text{pulse}} = 0.5 - 20 \text{ ms}$	165
Table 4.6 Saturation Current, Barrier Height, ideality factor, and series resistance of gold-nanodot/n-Si(100) structure in the diameter range of 50 – 98 nm at room temperature	179
Table 4.7 The saturation current, Schottky Barrier, ideality factor, and series resistance of gold nanodot/n-Si diode in the temperature range of 200 – 300 K	190

LIST OF FIGURES

		Page
Figure 2.1	Schematic of a generalized SPM (Binnig et al., 1999)	16
Figure 2.2	Principle of STM: Applying a negative sample voltage yields electron tunneling from occupied states at the surface into unoccupied states of the tip. Keeping the tunneling current constant while scanning the tip over the surface, the tip height follows a contour of constant local density of states (Voigtlander & Aachen, 2015)	17
Figure 2.3	Schematic view of two modes of operation in STM. (a) constant current mode, and (b) constant height mode. d is the gap between the tip and the sample, I_T and V_T are the tunneling current and bias voltage, respectively, and V_z is the feedback controlling the tip height along the z direction (Stroscio & Kaiser, 2013)	19
Figure 2.4	Schematic illustration of the operating principle of the AFM, which consist of a photo detector, a cantilever unit, scanner unit, source of laser unit and the optical unit (Bhushan, 2011)	21
Figure 2.5	The shape of the Lennard-Jones potential in qualitative form	23
Figure 2.6	Schematic picture of the AFM cantilever deflection	24

Figure 2.7	SEM images of AFM tips. (a) triangular cantilever tips, and (b) rectangular cantilever tips (Bhushan, 2011)	26
Figure 2.8	The principle of scanning protrusions appear wider, depressions narrower than they are in reality	27
Figure 2.9	Illustration of AFM image acquisition at constant force mode	29
Figure 2.10	Illustration of AFM image acquisition at constant height mode	30
Figure 2.11	Approach curves in the dynamic mode (operating frequency 328 kHz). Circles correspond to a Teflon surface and triangles to a gold surface. The squares correspond to mica and the vibration amplitude has been multiplied by 10, for the sake of comparison (Bhushan, 2011)	33
Figure 2.12	Illustration setup of an atomic force microscope operated in FM mode, as it is frequently realized for UHV applications (Bhushan, 2011)	35
Figure 2.13	Working point selection during semi-contact mode	41
Figure 2.14	Schematic of tapping mode used for surface roughness measurements (Bhushan, 2011)	42
Figure 2.15	The setup of a C-AFM electronic system configuration. The current is converted to voltage related to $V_o = I R_f$.	44

Figure 2.16	A schematic of two basic configurations for performing CAFM measurements. (a). the vertical configuration, and (b).the horizontal configuration	46
Figure 2.17	Simplified atomic potential diagrams for the tip-sample system with no applied field. (a) When the distance d is relatively large, and (b) When the distance d is shortened (tip and sample are very closed each other)	50
Figure 2.18	Ionic and atomic potential energy curves with applied external electric field, E_a	53
Figure 2.19	Field evaporation deposition, (a) Positive field and (b) Negative field. In this case, the gradient is not as intense on the tip apex. Then electrons from the sample will hit the large area close to the tip apex. Filed evaporation for the cations Au^+ will happen when the threshold field is reached, field close to 23.8 V/nm (Tsong, 1990)	55
Figure 2.20	STM image of oxidized Si(100) after application of multiple voltage pulse between sample and tip. Silicon oxide coverage is 2.2 ML. For these images, 10 pulses were applied with height of -6 V to -9 V to the tip. (b) The probability of dot formation as function of applied voltage. The threshold voltage is determined to be -8.2 V (Park et al., 2000)	59

Figure 2.21 Nano-Pt structures on Si substrate by direct STML deposition: (a) 6×9 dot array, each dot deposited with 50 consecutive pulses at negative 5.0 V pulse, 500 pA set current, and 50 ms duration time, where the average dot height and width are 4 and 22 nm, respectively; and (b) four lines drawn by 5.75 V pulse with different set current and pulse durations, 800 pA and 50 ms for lines 1 and 2, 800 pA and 10 μs for line 3, and 500 pA and 50 μs for line 4 (Houel et al., 2002)

60

Figure 2.22 UHV from a silver STM tip to a Si(111)-(7 × 7) surface by applying a voltage pulse. (a) The silver tip makes a mechanical point contact spontaneously with the Si(111)-(7 × 7) surface by field enhanced diffusion to the tip apex. (b) After a fixed period, the tip is extracted by feedback control. A silver nanodot is left on the surface because of the chemical bonds between silver and silicon atoms and a depletion region is formed around the nanodot (Fujita et al., 2003)

62

Figure 2.23 Nanostructures on Si substrates by direct STML deposition of sequential dots: sad STM image of Ag characters “A” by Ag-coated tip, (b) AFM image of Au lines by Au-coated tip (Fujita et al., 2003)

63

- Figure 2.24 An array of gold dots produced on HOPG by applying voltage pulses of -10 V for 1 ms to a gold-coated AFM tip (Song et al., 1997) 65
- Figure 2.25 Sequence of the gold nanowire fabrication is shown. (a) AFM image of the gold probing electrodes before AFM gold deposition is presented. (b) The gap between the electrodes is partially filled by a gold wire. (c) Final aspect of the nanowire bridging the probing electrodes is shown. Nano wire formed by the application of pulses of 0.5 ms at -20 V is presented (Calleja et al., 2001) 66
- Figure 2.26 3D topography images of a substrate region before (a) and after (b) the deposition of a square obtained from a 100×100 nm scan. The deposition was performed at 200 nm/s tip velocity, 1.28 nm^{-1} scan line density and 10 Hz pulse frequency (Melo and Brogueira, 2002) 67
- Figure 2.27 Experimental set-up. (a) Imaging: locating the region of the sample to be modified. (b) Lifting: we define and control the tip-sample distance d by applying a V_{bias} to the sample, and (c) After applying V_{pulse} , deposited structures are observed on the substrate. Notice the improvement in the quality of the scanned image due to a self-sharpening of the tip (Pumarol et al., 2005) 68
- Figure 2.28 AFM nanodot deposition mechanism diagram. A voltage pulse is applied to the tip and the substrate (Liu et al., 2013) 70

- Figure 2.29 (a) Deposited dots when applying 5 V voltage pulses with duration of 20 ms; (b) heights of D1, D2 and D3. The mean height of D1, D2 and D3 is 3.4 nm; (c) deposited dots when 6 V voltage pulses with duration of 20 ms; and (d) heights of D4, D5 and D6. The mean height of D4, D5 and D6 is 5.8 nm (Liu et al., 2013) 71
- Figure 2.30 Energy-band diagrams of metal-semiconductor contacts. (a) in separated systems, and (b) connected into one system. (c) as the gap δ is reduced and (d) δ becomes zero (Sze & Ng., 2007) 74
- Figure 2.31 Energy-band diagrams of metal-semiconductor contacts with the presence of surface states in semiconductors.(a) in separated systems, and (b) connected into one system.(c) as the gap δ is reduced and (d) δ becomes zero (Sze & Ng, 2007) 76
- Figure 2.32 Energy band diagram of metal n-type semiconductor under different biasing condition (a) thermal equilibrium, (b) forward bias, (c) reverse bias (Sze & Ng, 2007) 78
- Figure 2.33 Energy Band diagram between a metal surface and a vacuum (Sze & Ng, 2007) 82
- Figure 2.34 Energy band diagrams of a conventional metal-*n*-type semiconductor under forward, zero and reverse bias condition. ϕ_{Bn} is the barrier height at thermal equilibrium.

	ϕ_{B0} is the intrinsic barrier height. The barrier lowering under forward and reverse bias are $\Delta\phi_F$ and $\Delta\phi_R$, respectively (Sze & Ng, 2007)	84
Figure 2.35	Four basic transport mechanisms under forward bias condition; (a) thermionic emission over the barrier, (b) tunneling through the barrier, (c) carrier recombination in the depletion region, and (d) hole injection from the metal to the semiconductor (Sze & Ng, 2007)	85
Figure 2.36	Illustration of carrier transport mechanism for a Schottky barrier on n-doped silicon under an applied forward bias (Rhoderick and Williams, 1988)	89
Figure 2.37	Illustrated I - V curves for various diode sizes. The large diode curve has the expected exponential shape. The qualitative appearance of the curves changes drastically with decreasing diode size. The curves of the larger diodes have been scaled vertically (Smit et al., 2002)	94
Figure 2.38	Field and thermionic field emission under reverse bias condition (Rhoderick & Williams, 1988)	100
Figure 3.1	Detail of the SPM configuration	106
Figure 3.2	Omni-bearing FS-20V scanner	108
Figure 3.3	Specification and physical dimensions of the cantilever tip	109

Figure 3.4	SEM image of the cantilever and EDX/S pattern on one point at the end of the cantilever (inset)	109
Figure 3.5	There are three main units used to control the chamber environment condition: temperature control, vacuuming level control, and voltage supply control	112
Figure 3.6	Tip Polarity. V_B and V_P were always applied to the tip-sample respectively	113
Figure 3.7	Q-curve obtained from Q-curve tuning under vacuum condition at room temperature. The amplitude curve was red and phase curve was blue. The natural frequency for this particular cantilever was 227.926 KHz, quality factor was 658.019, amplitude was 0.1 Volt and Δf was 0.346 KHz	114
Figure 3.8	Plot of approach (red) and retract (blue) curves in ambient condition. The gradient chosen for sensitivity measurements and the baseline offset for deflection are both marked on this plot	116
Figure 3.9	$F(d)$ curve for three different bias voltage values were applied to the tip. (a) $V_{BIAS} = 0$ V, (b) $V_{BIAS} = 3$ V, and (c) $V_{BIAS} = 5$ V. It appears that the bias voltage increases, the curve shifts to the right. This indicates that the tip-sample distance increases with increasing the bias voltage	118

Figure 3.10	Tip movement trajectory in quasi coordinate on substrate surface in the executed program, in the deposition process of three nanodot	122
Figure 3.11	Deposition of tree gold nanodots on silicon substrate using an AFM non-contact. a) Imaging the area of interest using tapping-mode b) V_B was applied, tip-sample average separation was increased to d . A non contact image was taken. c) Deposition script was running: tip was translated to position of interest, V_p was applied, and d) Imaging the same area after deposition, three pulses were applied to area of (c), three nanodots successfully were deposited	123
Figure 3.12	The appearance of 2D-top view (a) and pseudo 3D-view (b) from three gold nanodots resulting from scanning result after deposition process was conducted	125
Figure 3.13	Result of line profile analysis. Shape, height and diameter of deposited nanodot gold	125
Figure 3.14	$(I-V)$ curve is generated on the $(I-V)$ console related to the location of the $(I-V)$ characterization	127
Figure 4.1	The results of tuning the Q-quality factor. The spring constant of the cantilever is 40 Nm^{-1} , the blue line is the phase, the red line is the amplitude, and the horizontal line is the set point	137

- Figure 4.2 Force-distance curve ($F-d$) yielded without applying bias voltage between tip and ($V_{\text{bias}} = 0$). The cantilever used is gold-coated with a spring constant of 40 N/m and diameter of the tip is 60 nm at room temperature in a vacuum condition 139
- Figure 4.3 Force-distance curve ($F-d$) obtained from the application of bias voltage of 6 V to tip-sample. The cantilever used is coated with gold, with a spring constant of 40 Nm⁻¹, amplitude set point = 0.85, reduced frequency = 0.99, and diameter of the tip is 60 nm at room temperature in a vacuum condition 142
- Figure 4.4 Calculated force-distance ($F-d$) curves against the reduced tip-sample separation d with electrostatic coupling. The parameter used are: reduced frequency $u = 0.99$, reduced amplitude $a = 0.85$, free oscillation amplitude $A_0 \approx 5.4$ nm, $Q \approx 706$, $k = 40$ Nm⁻¹, $k_{\text{elec}} = (1.287 \times 10^{-3}/V) V_{\text{BIAS}}^2$, and $k_{\text{vdW}} = 3.086 \times 10^{-4}$. These parameters correspond to typical experimental conditions and on the application of a bias voltage ranging from 1 - 9 V 144
- Figure 4.5 Reduced tip-sample separation against bias voltage shows a linear trend. The red line shows the tip-sample distance associated with a bias voltage of 6 V between the tip and sample 147

Figure 4.6	Relevant distance for the tip-sample geometry. d is the instantaneous tip-sample separation, D is the average tip-sample separation and A is the oscillation amplitude (Garcia and Perez, 2002)	148
Figure 4.7	SEM image in a 2D view of gold nanodot that have deposited, by applying a voltage pulses between 19 – 42 V and pulse duration of 3 ms at a fixed bias voltage of 6 V	149
Figure 4.8	EDX pattern analysis and the material composition (Element and Wt%). Au is detected in the dot deposition result	150
Figure 4.9	3D image of a several rows of gold nanodot deposited with voltage and pulse duration are varied. White circle shows where the gold nanodot cannot successfully deposit. It appears that the bias voltage between the tip-sample is the determining for the successes of the gold nanodot deposition process	153
Figure 4.10	3D image of a few series of gold nanodot deposited with different voltage pulses polarity. At the initial stage of deposition, the deposited gold nanodots have a relatively large dimension; wide and high (row number 1). The positive voltage pulse is used for dot series A, while the negative voltage pulse is used for dot series B	154

- Figure 4.11 The line profiles of the dot rows A and B that deposited using different voltage pulse polarity. The pulse duration is fixed, $\Delta t = 2$ ms. The maximum height for row A is around 6.6 nm, and for row B is around 1.6 nm 156
- Figure 4.12 Scanned image of three gold nanodots deposited with V_{PULSE} different but with the same pulse duration ($\Delta t_{\text{PULSE}} = 3$ ms). These results were obtained with the same tip, oscillation amplitude, and the same tip-sample bias voltage $V = 6$ V 157
- Figure 4.13 The graph that shows the relationship between the deposition parameters, V_P against the gold nanodot dimension at a fixed pulse duration of 3 ms 160
- Figure 4.14 2D (left) and 3D (right) viewed of three gold nanodots fabricated by applying a voltage pulse with amplitudes of -38 V, -40 V and -42 V, while the pulse duration is kept constant at 3 ms. It's appears that gold nanodots shape is no longer circular but more like a square shape 161
- Figure 4.15 Scanning image of three gold nanodots deposited with different Δt_{PULSE} and with the same pulse amplitude 163
- Figure 4.16 2D AFM image and the line profile generated; (a) Dot number 1 and number 2 were deposited using voltage pulse duration of 1 ms and 5 ms, while the amplitude of the voltage pulse is kept constant of -32 V, while (b) The dot

	number 3, 4 and 5 were deposited using voltage pulse duration of 1 ms, 5 ms and 10 ms while the voltage pulse amplitude was kept constant at -32 V	164
Figure 4.17	The graph that shows the relationship between the deposition parameters, V_P against the gold nanodot dimension at a fixed pulse duration of 3 ms	166
Figure 4.18	(a). Various formations of gold nanodots arrangement that forms a row, line, circle, square, and arrays, which were deposited with varying parameters, both pulse amplitude and pulse duration. (b). several rows of dot deposited with varied parameters (amplitude and pulse duration), it appears that dot dimensions are strong influenced by voltage pulse amplitude	167
Figure 4.19	Probability of deposition while ramps the voltage pulse amplitude, with a single pulse each time, and at fixed tip-sample distance average of d (specified by tip-sample bias voltage of 6 V). The tip was Au-coated and in graph each point corresponds to 10 trials	168
Figure 4.20	FESEM images of the cantilever tip; (a) before, and (b) after deposition process was carried out. It seems that the tip is worn out due to reduce the material transferred from the tip after deposition process	169

Figure 4.21	The AFM image in 2D view and the line profile of five dots fabricated by using AFM, which have a diameter in the range of 50 -98 nm	171
Figure 4.22	The semi-logarithmic (I - V) characteristics measurements of Au-n type silicon nanostructure at room temperature for the dot diameter of 50 nm, 60 nm 72 nm, 86 nm, and 98 nm. Forward (a) and reverse (b) bias condition	173
Figure 4.23	Dependence of ideality factor (n) and barrier height (ϕ_B) to the dot diameter. By increasing the dot diameter, the ideality factor increases. The dependence of barrier height to the dot diameter with increasing the dot diameter shows the barrier height increases	175
Figure 4.24	The equivalent circuit of a diode, which consists of the composition of several resistors. (a) Device under test (DUT), (b) resistance that contribute to the series resistance (c) equivalent circuit of DUT	177
Figure 4.25	Diameter dependence of series resistance of gold-nanodot/n-Si(100) structure in the diameter range of 50 – 98 nm at room temperature, shows that with the dot diameter increasing, the series resistance value decreases	178
Figure 4.26	The forward bias $\ln I$ vs $\ln V$ characteristics of the gold nanodot/ n -Si(100) at room temperature for various diameter range of 50 - 98 nm	180

Figure 4.27	Experimental (I - V) characteristics for various diode sizes. It appears that the curves changes drastically with decreasing diode size, and reverse current do not experience saturation	182
Figure 4.28	2D AFM image of nine gold nanodots deposited with voltage amplitude of -26 V and pulse duration of 2 ms. It appears that nine gold nanodot have a uniform shape with average height is 4.4 nm, while the average diameter is 60 nm	183
Figure 4.29	The experimental semi-logarithmic current-voltage (I - V) characteristics of gold nanodot/ n -Si Schottky diode at various temperatures under (a) forward bias and (b) reverse bias with the diameter of 60 nm	184
Figure 4.30	Temperature dependence of the ideality factor and barrier height for the gold nanodot/ n -Si Schottky barrier	186
Figure 4.31	The temperature dependence of the series resistances obtained from Cheung and Cheung's methods for gold nanodot/ n -Si	188
Figure 4.32	$\ln(I_0/T^2)$ vs $1000/T$ plots gold nanodot/ n -Si(100) Schottky diodes showing non-linearity below 225 K	189